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April 1st, 2010 Renesas Electronics Corporation

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R1LV0408D Series

4M SRAM (512-kword \times 8-bit)

REJ03C0310-0100 Rev.1.00 May.24.2007

Description

The R1LV0408D is a 4-Mbit static RAM organized 512-kword \times 8-bit, fabricated by Renesas's high-performance 0.15 μ m CMOS and TFT technologies. R1LV0408D Series has realized higher density, higher performance and low power consumption. The R1LV0408D Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It has packaged in 32-pin SOP, 32-pin TSOP II and 32-pin STSOP.

Features

• Single 3 V supply: 2.7 V to 3.6 V

• Access time: 55/70 ns (max)

• Power dissipation:

— Standby: 3 μW (typ)

• Equal access and cycle times

- Common data input and output.
 - Three state output
- Directly TTL compatible.
 - All inputs and outputs
- Battery backup operation.

R1LV0408D Series

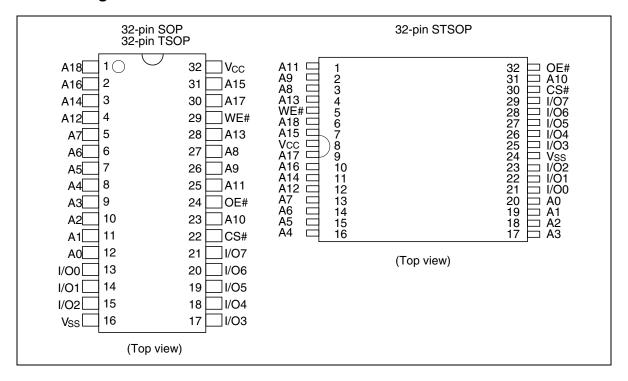
Ordering Information

Type No.	Access time	Package
R1LV0408DSP-5S%	55 ns	525-mil 32-pin plastic SOP (32P2M-A)
R1LV0408DSP-7L%	70 ns	
R1LV0408DSB-5S%	55 ns	400-mil 32-pin plastic TSOP II (32P3Y-H)
R1LV0408DSB-7L%	70 ns	
R1LV0408DSA-5S%	55 ns	8mm × 13.4mm STSOP (32P3K-B)
R1LV0408DSA-7L%	70 ns	

%: Temperature version; see table below.

%	Temperature Range
R	0 to +70°C
I	–40 to +85°C

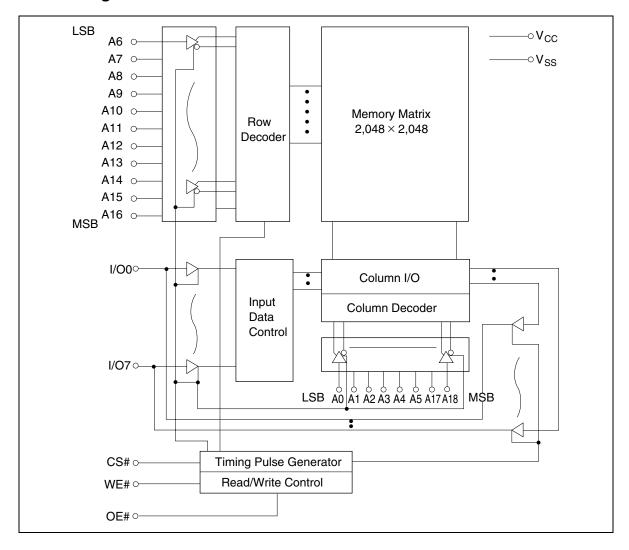
Pin Arrangement



Pin Description

Pin name	Function
A0 to A18	Address input
I/O0 to I/O7	Data input/output
CS# (CS)	Chip select
OE# (OE)	Output enable
WE# (WE)	Write enable
V _{cc}	Power supply
V _{ss}	Ground

Block Diagram



Operation Table

WE#	CS#	OE#	Mode	V _{cc} current	I/O0 to I/O7	Ref. cycle
×	Н	×	Not selected	elected I _{SB} , I _{SB1}		_
Н	L	Н	Output disable	I _{cc}	High-Z	_
Н	L	L	Read	I _{cc}	Dout	Read cycle
L	L	Н	Write	I _{cc}	Din	Write cycle (1)
L	L	L	Write	I _{cc}	Din	Write cycle (2)

Note: H: V_{IH} , L: V_{IL} , \times : V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol		Unit	
Power supply voltage relative to V _{ss}	V _{cc}		-0.5 to +4.6	V
Terminal voltage on any pin relative to V _{ss}	V _T	-0.	5*1 to V _{cc} + 0.5*2	V
Power dissipation	P _T		0.7	W
Operating temperature	Topr	R ver.	0 to +70	°C
		I ver.	-40 to +85	
Storage temperature range	Tstg		-65 to +150	°C
Storage temperature range under bias	Tbias	R ver.	0 to +70	°C
		I ver.	-40 to +85	1

Notes: 1. V_{τ} min: -3.0 V for pulse half-width ≤ 30 ns.

2. Maximum voltage is +4.6 V.

DC Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit	
Supply voltage	V _{cc}	2.7	3.0	3.6	V	
		V _{ss}	0	0	0	V
Input high voltage		V _{IH}	2.2	_	V _{cc} + 0.3	V
Input low voltage		V _{IL}	-0.3* ¹	_	0.6	V
Ambient temperature range	ent temperature range R ver.		0	_	+70	°C
	I ver.		-40	_	+85	

Note: 1. V_{IL} min: -3.0 V for pulse half-width ≤ 30 ns.

DC Characteristics

	Para	meter	Symbol	Min	Тур	Max	Unit	Test conditions
Input leak	kage curre	ent	I _{LI}	_	_	1	μΑ	Vin = V _{ss} to V _{cc}
Output le	akage cur	rent	I _{LO}	_	_	1	μА	$CS\# = V_{IH}$ or $OE\# = V_{IH}$ or $WE\# = V_{IL}$ or $V_{I/O} = V_{SS}$ to V_{CC}
Operating	g current		I _{cc}		_	10	mA	$CS\# = V_{IL},$ Others = V_{IH}/V_{IL} , $I_{I/O} = 0$ mA
Average	operating	current	I _{CC1}			25	mA	Min. cycle, duty = 100%, CS# = V_{IL} , Others = V_{IH}/V_{IL} $I_{I/O}$ = 0 mA
			I _{CC2}			5	mA	$\begin{aligned} &\text{Cycle time} = 1 \mu\text{s}, \\ &\text{duty} = 100\%, \\ &I_{\text{\tiny I/O}} = 0 \text{ mA, CS\#} \leq 0.2 \text{ V}, \\ &V_{\text{\tiny IH}} \geq V_{\text{\tiny CC}} - 0.2 \text{ V}, V_{\text{\tiny IL}} \leq 0.2 \text{ V} \end{aligned}$
Standby	current		I _{SB}		0.1*1	0.3	mA	CS# = V _{IH}
Standby	-5S%	to +85°C	I _{SB1}			10	μΑ	Vin ≥ 0 V, CS# ≥ V _{cc} – 0.2 V
current		to +70°C	I _{SB1}			8	μΑ	Average values
		to +40°C	I _{SB1}		— 3 μA			
		to +25°C	I _{SB1}		1*1	2.5	μΑ	
	-7L%	to +85°C	I _{SB1}		_	20	μΑ	
		to +70°C	I _{SB1}		_	16	μΑ	
		to +40°C	I _{SB1}	_	_	10	μΑ	
		to +25°C	I _{SB1}		1*1	10	μΑ	
Output low voltage			V _{OL}			0.4	V	I _{oL} = 2.1 mA
			V _{OL2}			0.2	V	$I_{OL} = 100 \mu A$
Output high voltage			V _{OH}	2.4		_	V	I _{OH} = -1.0 mA
			V _{OH2}	$V_{\rm cc} - 0.2$	_	_	V	$I_{OH} = -0.1 \text{ mA}$

Note: 1. Typical values are at $V_{cc} = 3.0 \text{ V}$, $Ta = +25^{\circ}\text{C}$ and specified loading, and not guaranteed.

Capacitance

 $(Ta = +25^{\circ}C, f = 1.0 \text{ MHz})$

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions	Note
Input capacitance	Cin	_	_	8	рF	Vin = 0 V	1
Input/output capacitance	C _{I/O}	_	_	10	рF	$V_{I/O} = 0 V$	1

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics

 $(Ta = 0 \text{ to } +70^{\circ}\text{C} / -40 \text{ to } +85^{\circ}\text{C}, V_{cc} = 2.7 \text{ V to } 3.6 \text{ V})$

Test Conditions

• Input pulse levels: $V_{IL} = 0.4 \text{ V}, V_{IH} = 2.4 \text{ V}$

• Input rise and fall time: 5 ns

• Input and output timing reference levels: 1.5 V

 • Output load: 1 TTL Gate + C_L (50 pF) (R1LV0408D-5S%) 1 TTL Gate + C_L (100 pF) (R1LV0408D-7L%)

(Including scope and jig)

Note: Temperature range depends on R/I-version. Please see table on page 2.

Read Cycle

			R1LV				
		-59	5%	-71	_%		
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read cycle time	t _{RC}	55	_	70	_	ns	
Address access time	t _{AA}	_	55	_	70	ns	
Chip select access time	t _{co}	_	55	_	70	ns	
Output enable to output valid	t _{oe}	_	30	_	35	ns	
Chip select to output in low-Z	t _{LZ}	10	_	10	_	ns	2
Output enable to output in low-Z	t _{oLZ}	5	_	5	_	ns	2
Chip deselect to output in high-Z	t _{HZ}	0	20	0	25	ns	1, 2
Output disable to output in high-Z	t _{ohz}	0	20	0	25	ns	1, 2
Output hold from address change	t _{oн}	10		10	_	ns	





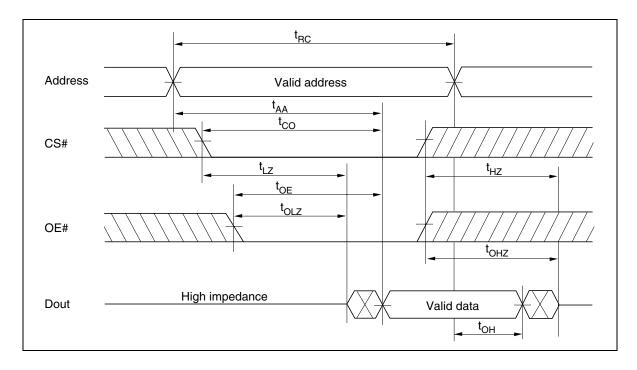
Write Cycle

			R1LV				
		-59	S%	-71	_%		
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	t _{wc}	55	<u> </u>	70		ns	
Chip selection to end of write	t _{cw}	50	_	60	_	ns	4
Address setup time	t _{AS}	0	_	0	_	ns	5
Address valid to end of write	t _{AW}	50	<u> </u>	60		ns	
Write pulse width	t _{wP}	40	<u> </u>	50		ns	3, 12
Write recovery time	t _{wR}	0	_	0		ns	6
Write to output in high-Z	t _{whz}	0	20	0	25	ns	1, 2, 7
Data to write time overlap	t _{DW}	25	<u> </u>	30		ns	
Data hold from write time t _{DH}		0	_	0		ns	
Output active from end of write	t _{ow}	5	_	5	_	ns	2
Output disable to output in high-Z	t _{oHZ}	0	20	0	25	ns	1, 2, 7

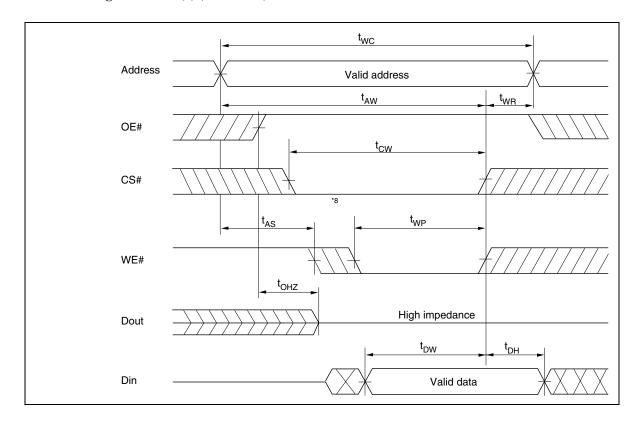
- Notes: 1. t_{HZ} , t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 - 2. This parameter is sampled and not 100% tested.
 - 3. A write occurs during the overlap (t_{wP}) of a low CS# and a low WE#. A write begins at the later transition of CS# going low or WE# going low. A write ends at the earlier transition of CS# going high or WE# going high. t_{wP} is measured from the beginning of write to the end of write.
 - 4. t_{cw} is measured from CS# going low to the end of write.
 - 5. t_{AS} is measured from the address valid to the beginning of write.
 - 6. t_{we} is measured from the earlier of WE# or CS# going high to the end of write cycle.
 - 7. During this period, I/O pins are in the output state so that the input signals of the opposite phase to the outputs must not be applied.
 - 8. If the CS# low transition occurs simultaneously with the WE# low transition or after the WE# transition, the output remain in a high impedance state.
 - 9. Dout is the same phase of the write data of this write cycle.
 - 10. Dout is the read data of next address.
 - 11. If CS# is low during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the outputs must not be applied to them.
 - 12. In the write cycle with OE# low fixed, t_{WP} must satisfy the following equation to avoid a problem of data bus contention. $t_{WP} \ge t_{DW} \min + t_{WHZ} \max$

Timing Waveform

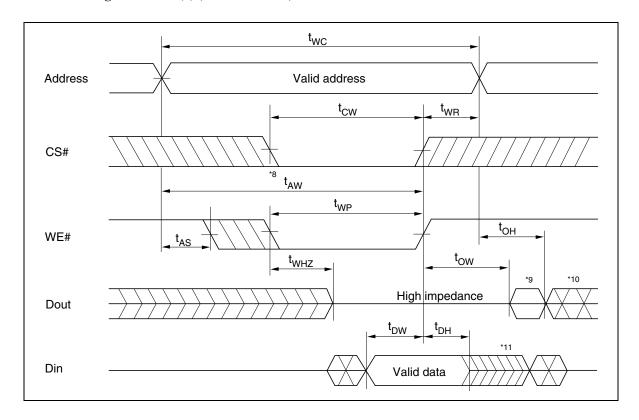
Read Timing Waveform (WE# = $V_{\text{\tiny IH}}$)



Write Timing Waveform (1) (OE# Clock)



Write Timing Waveform (2) (OE# Low Fixed)



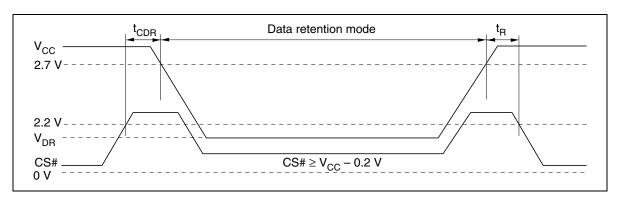
Low V_{CC} Data Retention Characteristics

 $(Ta = 0 \text{ to } +70^{\circ}\text{C} \text{ / } -40 \text{ to } +85^{\circ}\text{C})$

	Paramet	Symbol	Min	Тур	Max	Unit	Test conditions	
V _{cc} for data retention			$V_{_{\mathrm{DR}}}$	2	_	_	V	CS# ≥ V _{cc} – 0.2 V, Vin ≥ 0 V
Data	-5S%	to +85°C	CCDR	_	_	10	μΑ	$V_{cc} = 3.0 \text{ V}, \text{ Vin} \ge 0 \text{ V}$
retention current		to +70°C	I _{CCDR}	_	_	8	μА	CS# ≥ V _{cc} – 0.2 V
Carrent		to +40°C	I _{CCDR}	_	_	3	μА	Average values
		to +25°C	CCDR	_	1 * ¹	2.5	μΑ	
	-7L%	to +85°C	I _{CCDR}	_	_	20	μΑ	
		to +70°C	I _{CCDR}	_		16	μΑ	
		to +40°C	I _{CCDR}	_	_	10	μΑ	
		to +25°C	CCDR	_	1 * ¹	10	μΑ	
Chip deselect to data retention time			t _{cdr}	0		_	ns	See retention waveform
Operation recovery time			t _R	5			ms	

Note: 1. Typical values are at $V_{cc} = 3.0 \text{ V}$, $Ta = +25^{\circ}\text{C}$ and specified loading, and not guaranteed.

Low V_{CC} Data Retention Timing Waveform (CS# Controlled)



Revision History

R1LV0408D Series Data Sheet

Rev.	Date		Contents of Modification			
		Page	Description			
0.01	Dec. 25, 2006	_	Initial issue			
1.00	May. 24, 2007	6	DC Characteristics			
			I _{SB1} (-5S%) (to +25°C) max: 3 μA to 2.5 μA			
		12	Low V _{CC} Data Retention Characteristics			
			I _{CCDR} (-5S%) (to +25°C) max: 3 μA to 2.5 μA			
			Deletion of note 2			

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